# CRSM052N10N3

SkyMOS3 N-MOSFET 100V, 4.4mΩ, 60A

## Features

- Uses CRM(CQ) advanced SkyMOS3 technology
- Extremely low on-resistance $R_{DS(on)}$
- Excellent $Q_g$x$R_{DS(on)}$ product(FOM)
- Qualified according to JEDEC criteria

## Applications

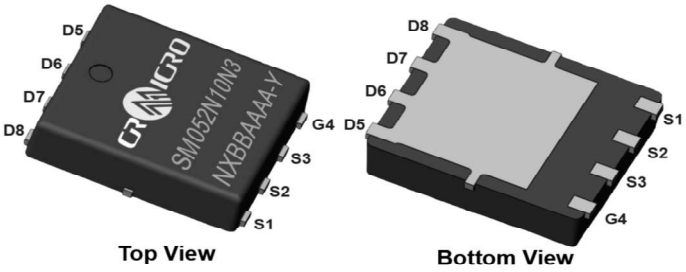
- Synchronous Rectification for Converters
- Charger for Mobile Devices
- Battery management System

## Product Summary

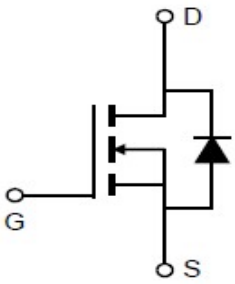
| | |
|---|---|
| $V_{DS}$ | 100V |
| $R_{DS(on).typ}$ | 4.4mΩ |
| $I_D$ | 60A |

***100% DVDS Tested***

***100% Avalanche Tested***




CRSM052N10N3




## Package Marking and Ordering Information

| Part # | Marking | Package | Packing | Reel Size | Tape Width | Qty |
|---|---|---|---|---|---|---|
| CRSM052N10N3 | SM052N10N3 | DFN56 | Tape | N/A | N/A | 5000pcs |

## Absolute Maximum Ratings

| Parameter | Symbol | Value | Unit |
|---|---|---|---|
| Drain-source voltage | $V_{DS}$ | 100 | V |
| Continuous drain current<br>$T_C$ = 25°C (Silicon limit)<br>$T_C$ = 25°C (Package limit)<br>$T_C$ = 100°C (Silicon limit) | $I_D$ | <br>100<br>60<br>64 | A |
| Pulsed drain current ($T_C$ = 25°C, $t_p$ limited by $T_{jmax}$) | $I_{D\ pulse}$ | 240 | A |
| Avalanche energy, single pulse ($I_D$ = 47A, Rg=25Ω)[1] | $E_{AS}$ | 541 | mJ |
| Gate-Source voltage | $V_{GS}$ | ±20 | V |
| Power dissipation ($T_C$ = 25°C) | $P_{tot}$ | 97 | W |
| Operating junction and storage temperature | $T_j$ , $T_{stg}$ | -55...+150 | °C |
| Soldering temperature, wave soldering only allowed at leads (1.6mm from case for 10s) | Tsold | 260 | °C |

※. Notes:

1.EAS is tested at starting Tj = 25℃, L = 0.5mH, IAS =47A, VGS = 10V.


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## Thermal Resistance

| Parameter | Symbol | Max | Unit |
|---|---|---|---|
| Thermal resistance, junction – case. | $R_{thJC}$ | 1.29 | °C/W |
| Thermal resistance, junction – ambient(min. footprint) | $R_{thJA}$ | 52 | |

## Electrical Characteristic (at Tj = 25 °C, unless otherwise specified)

| Parameter | Symbol | Value | | | Unit | Test Condition |
|---|---|---|---|---|---|---|
| | | min. | typ. | max. | | |
| **Static Characteristic** | | | | | | |
| Drain-source breakdown voltage | $BV_{DSS}$ | 100 | - | - | V | $V_{GS}$=0V, $I_D$=250uA |
| | | 100 | - | - | V | $V_{GS}$=0V, $I_D$=1mA |
| Gate threshold voltage | $V_{GS(th)}$ | 2.3 | 3.3 | 4.3 | V | $V_{DS}$=$V_{GS}$,$I_D$=250uA |
| Zero gate voltage drain current | $I_{DSS}$ | -<br>- | -<br>- | 1<br>100 | μA | $V_{DS}$=100V,$V_{GS}$=0V<br>$T_j$=25°C<br>$T_j$=125°C |
| Gate-source leakage current | $I_{GSS}$ | 0 | - | ±100 | nA | $V_{GS}$=±20V,$V_{DS}$=0V |
| Drain-source on-state resistance | $R_{DS(on)}$ | - | 4.4 | 5.2 | mΩ | VGS=10V, ID=30A |
| Transconductance | $g_{fs}$ | - | 45.3 | - | S | $V_{DS}$=5V, $I_D$=30A |
| **Dynamic Characteristic** | | | | | | |
| Input Capacitance | $C_{iss}$ | - | 5333 | - | pF | $V_{GS}$=0V, $V_{DS}$=50V, f=1MHz |
| Output Capacitance | $C_{oss}$ | - | 622 | - | | |
| Reverse Transfer Capacitance | $C_{rss}$ | - | 32 | - | | |
| Gate Total Charge | $Q_G$ | - | 89.5 | - | nC | $V_{GS}$=10V, $V_{DS}$=50V, $I_D$=30A |
| Gate-Source charge | $Q_{gs}$ | - | 33.4 | - | | |
| Gate-Drain charge | $Q_{gd}$ | - | 22.0 | - | | |
| Turn-on delay time | $t_{d(on)}$ | - | 26.1 | - | ns | $V_{GS}$=10V, $V_{DD}$=50V, $R_{G_ext}$=2.7Ω |
| Rise time | $t_r$ | - | 44.1 | - | | |
| Turn-off delay time | $t_{d(off)}$ | - | 55.3 | - | | |
| Fall time | $t_f$ | - | 23.5 | - | | |
| Gate resistance | $R_G$ | - | 2.2 | - | Ω | $V_{GS}$=0V, $V_{DS}$=0V, f=1MHz |


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## Body Diode Characteristic

| Parameter | Symbol | Value | | | Unit | Test Condition |
|---|---|---|---|---|---|---|
| | | min. | typ. | max. | | |
| Body Diode Forward Voltage | $V_{SD}$ | - | 0.85 | 1.4 | V | $V_{GS}$=0V,$I_{SD}$=30A |
| Body Diode Reverse Recovery Time | $t_{rr}$ | - | 61.7 | - | ns | $I_F$=30A,dI/dt=100A/μs |
| Body Diode Reverse Recovery Charge | $Q_{rr}$ | - | 131.5 | - | nC | |


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## Typical Performance Characteristics

Fig 1: Output Characteristics

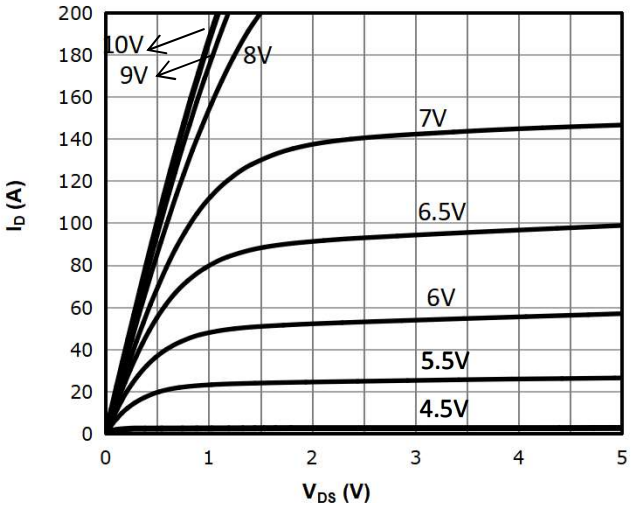



Fig 2: Transfer Characteristics

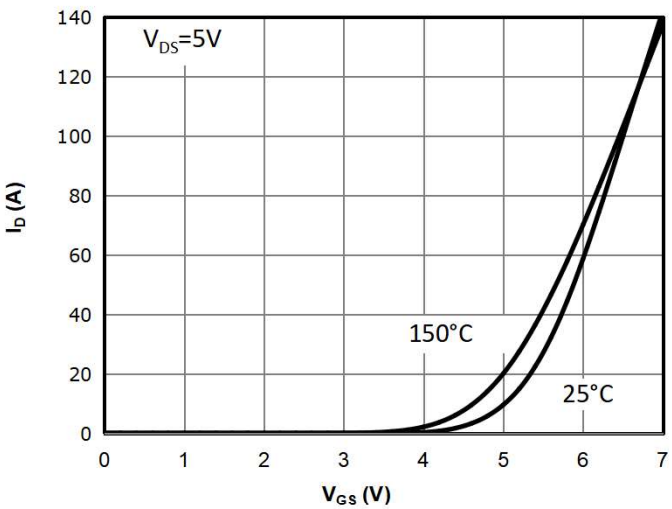



Fig 3: Rds(on) vs Drain Current and Gate Voltage

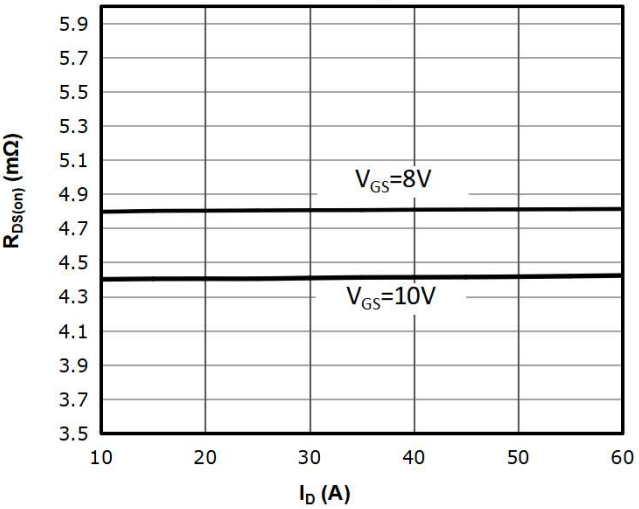



Fig 4: Rds(on) vs Gate Voltage

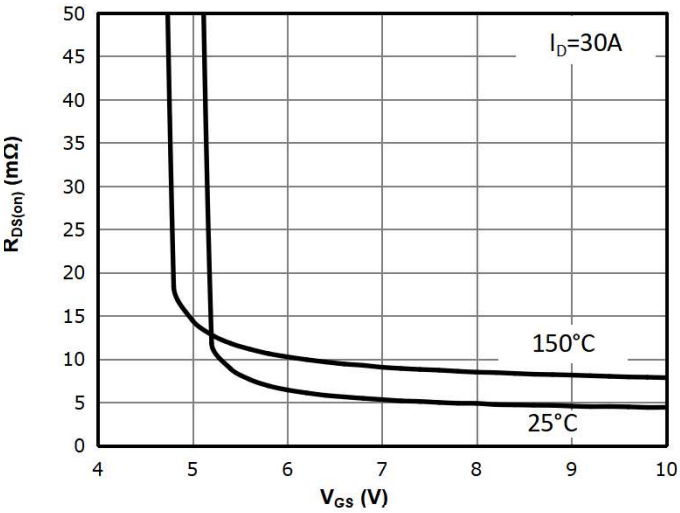



Fig 5: Rds(on) vs. Temperature

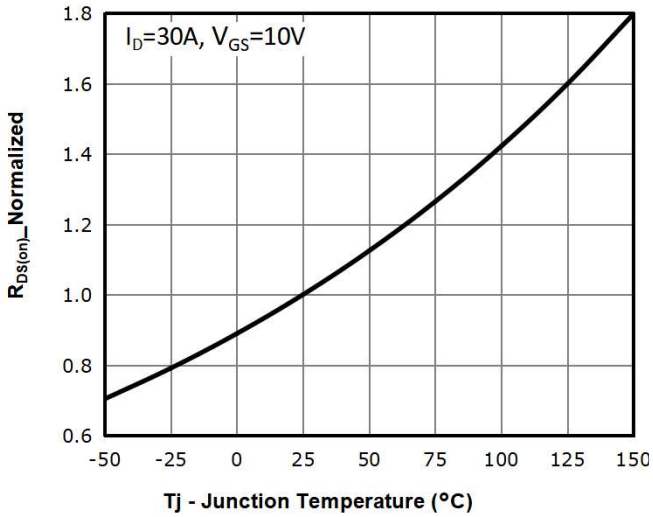
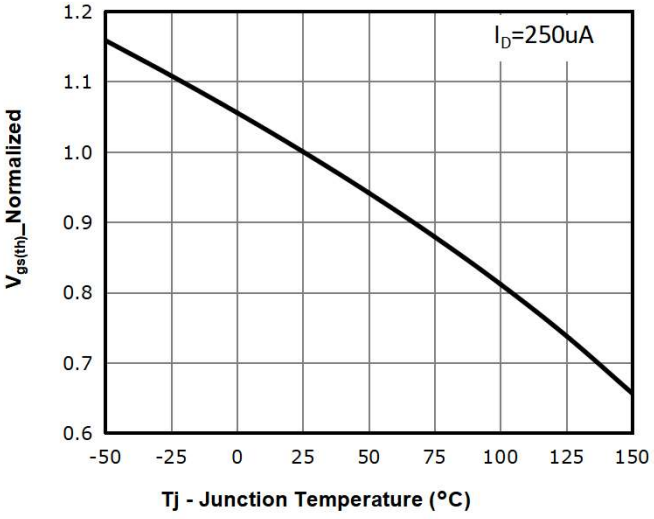



Fig 6: Vgs(th) vs. Temperature





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Fig 7: BVdss vs. Temperature

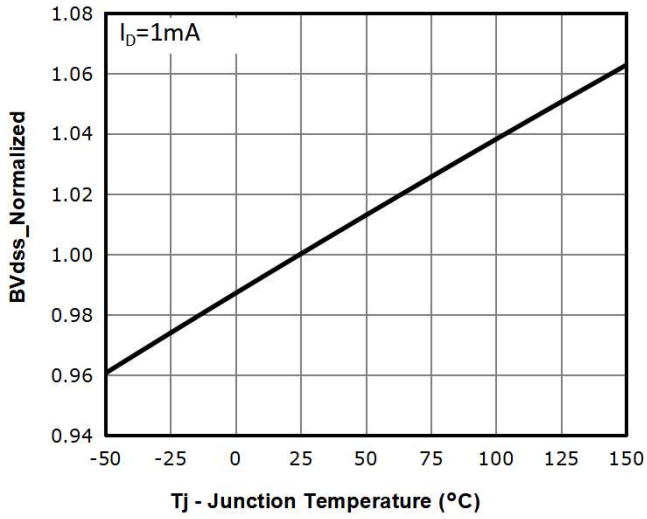



Fig 8: Capacitance Characteristics

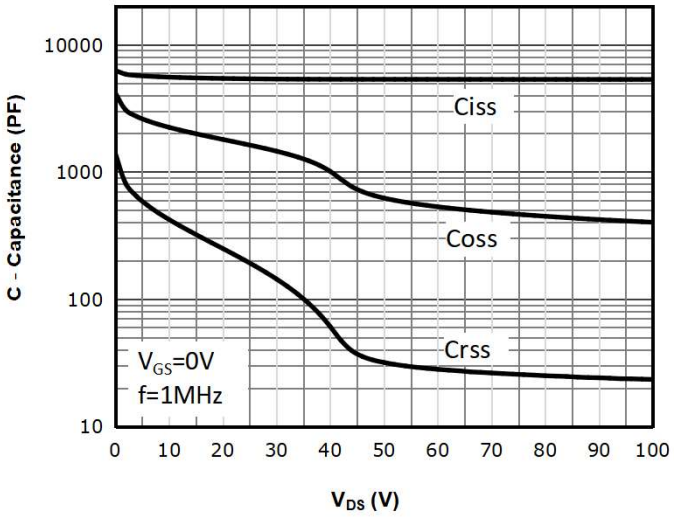



Fig 9: Gate Charge Characteristics

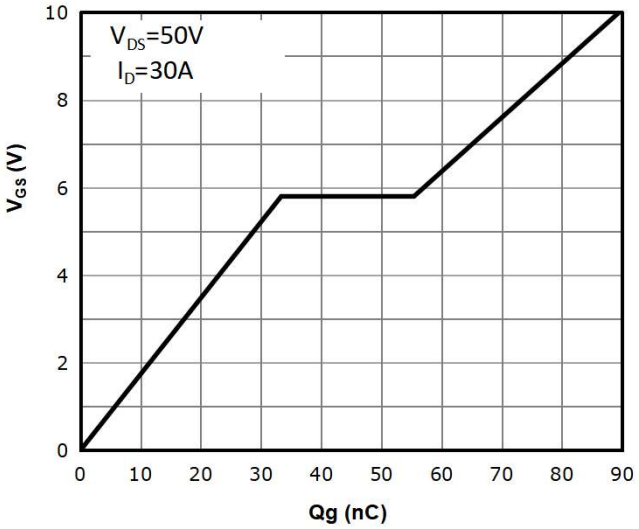



Fig 10: Body-diode Forward Characteristics

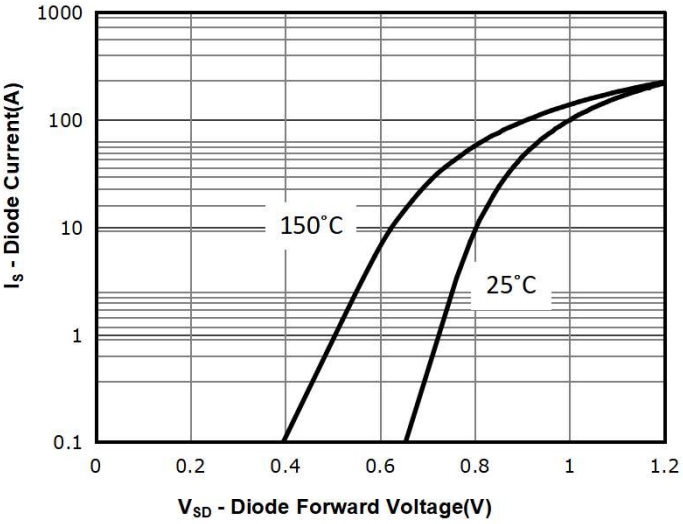



Fig 11: Power Dissipation

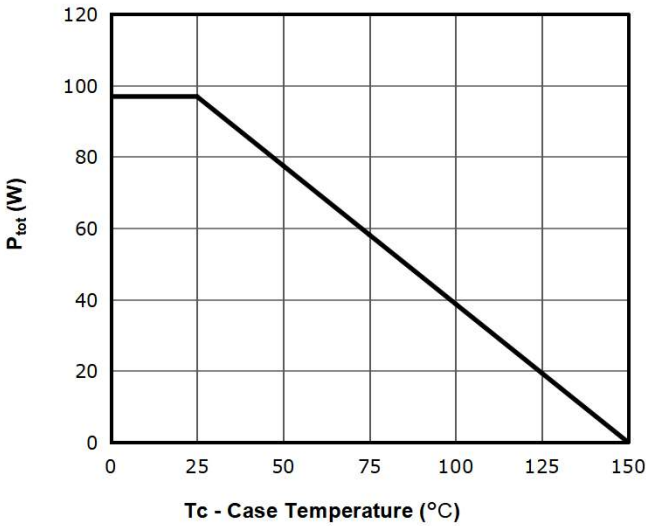
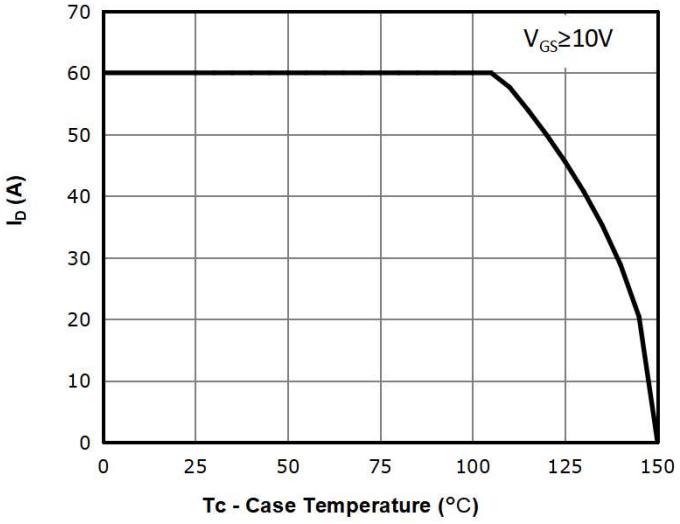



Fig 12: Drain Current Derating





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Fig 13: Safe Operating Area

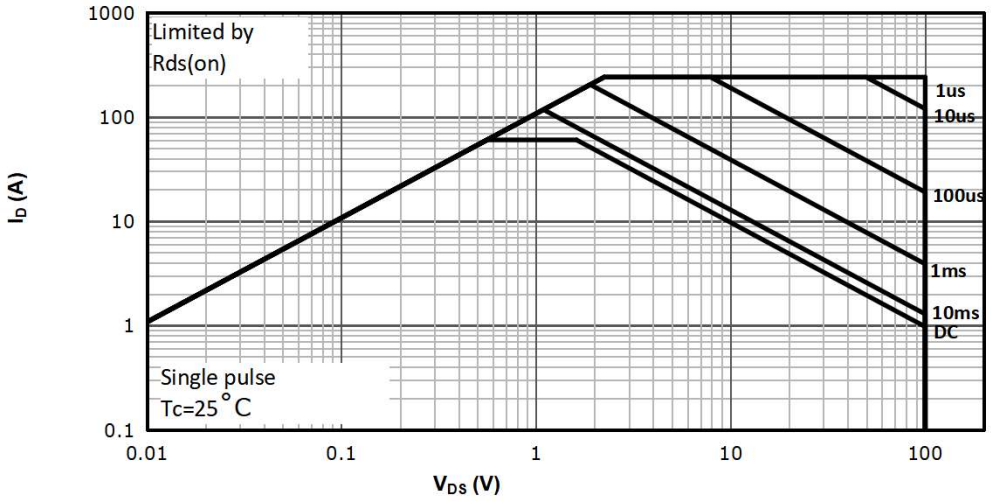
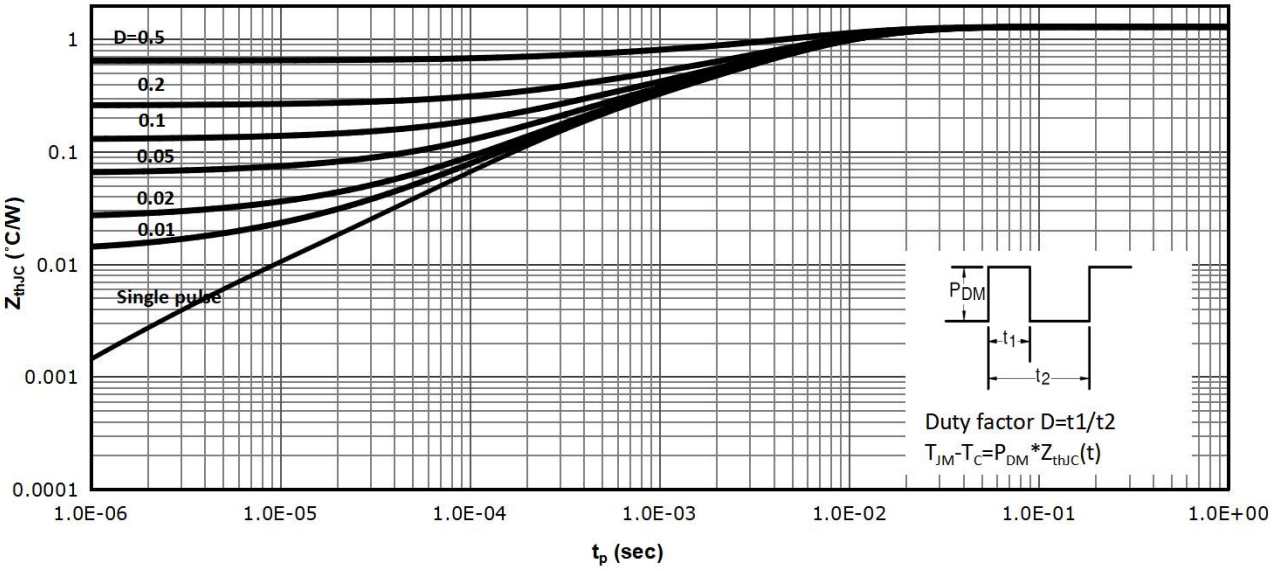



Fig 14: Max. Transient Thermal Impedance

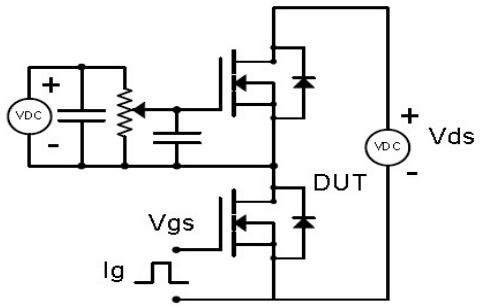


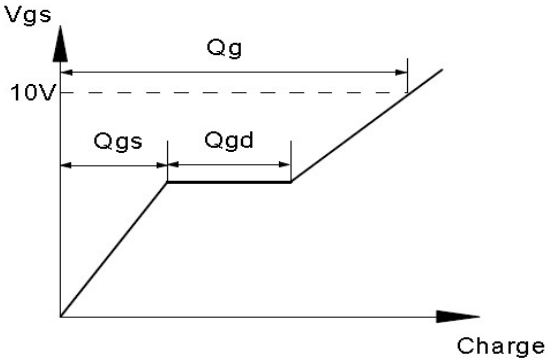


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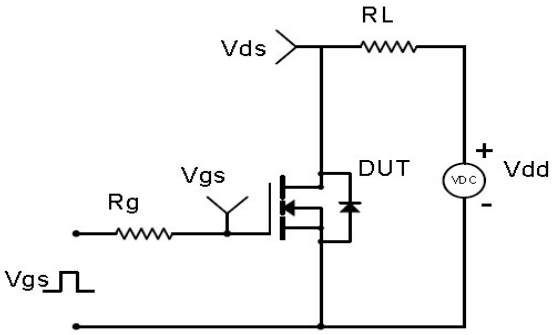
## Test Circuit & Waveform

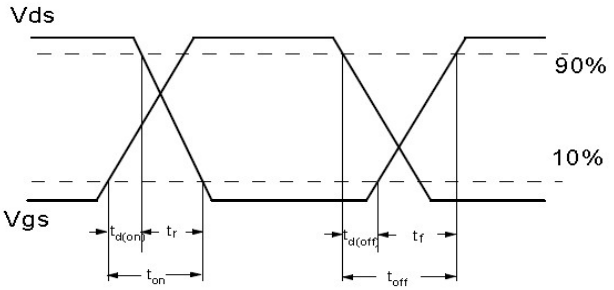
Gate Charge Test Circuit & Waveform



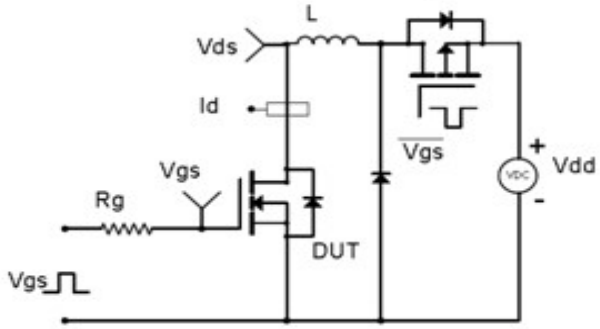



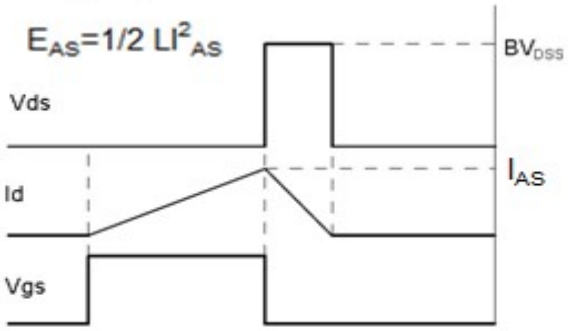

Resistive Switching Test Circuit & Waveforms



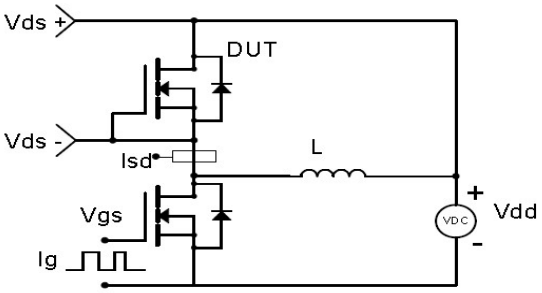



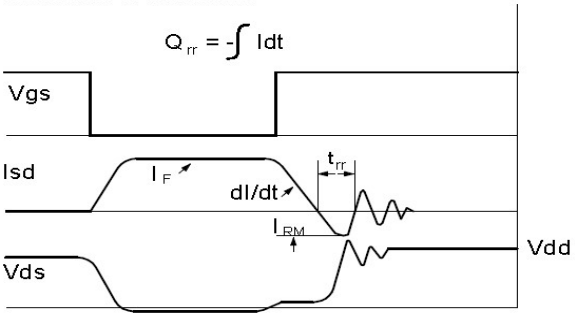

Unclamped Inductive Switching (UIS) Test Circuit & Waveforms




Diode Recovery Test Circuit & Waveforms

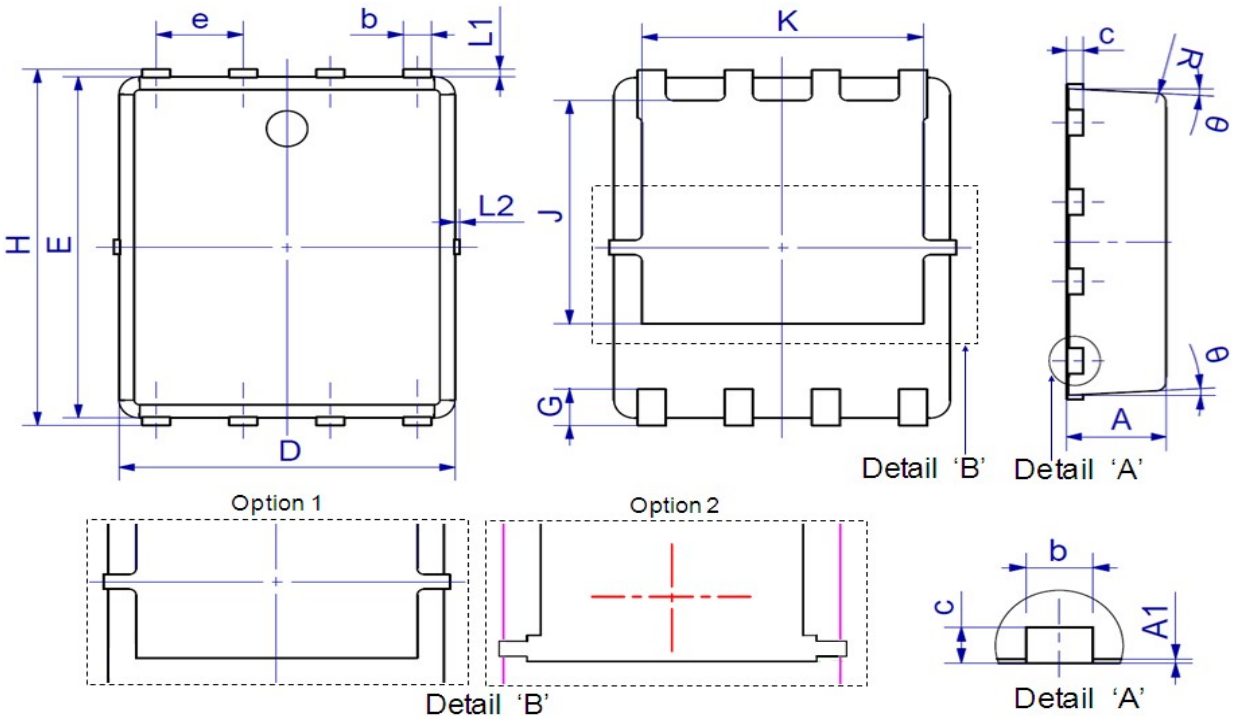




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## Package Outline: DFN5X6




| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|---|---|---|---|---|
| | Min. | Max. | Min. | Max. |
| A | 0.80 | 1.20 | 0.031 | 0.047 |
| A1 | 0.00 | 0.05 | 0.000 | 0.002 |
| b | 0.30 | 0.51 | 0.012 | 0.020 |
| c | 0.15 | 0.35 | 0.006 | 0.014 |
| D | 4.80 | 5.40 | 0.189 | 0.213 |
| e | 1.27 BSC | | 0.050 BSC | |
| E | 5.66 | 6.06 | 0.223 | 0.239 |
| G | 0.30 | 0.71 | 0.012 | 0.028 |
| H | 5.90 | 6.35 | 0.232 | 0.250 |
| J | 3.32 | 3.92 | 0.131 | 0.154 |
| K | 3.61 | 4.25 | 0.142 | 0.167 |
| L1 | 0.05 | 0.25 | 0.002 | 0.010 |
| L2 | 0.00 | 0.15 | 0.000 | 0.006 |
| R | 0.25 REF | | 0.010 REF | |
| θ | 0° | 12° | 0° | 12° |


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## Marking




NOTE:
NXBBAAAA-Y
N —Wire Bond code
X —Assembly location code
BB —Fab code
AAAA —Lot code
Y —Bin code


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## Revision History

| Revision | Date | Major changes |
|---|---|---|
| 1.0 | 2024/10/18 | Release of Preliminary version. |

## Disclaimer

Unless otherwise specified in the datasheet, the product is designed and qualified as a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability, such as automotive, aviation/aerospace and life-support devices or systems.

Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.

CRM(CQ) reserves the right to improve product design, function and reliability without notice.


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